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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Complete if Known

Application Number	Unassigned
Filing Date	March 11, 2004
First Named Inventor	KAWAHARA et al.
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	403001

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[illegible][illegible]

OTHER - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Doc. No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number (s), publisher, city and/or country where published.	Translation	
			Yes	No**
CL	A2	BLIN, et al., "Study of the initial steps of ALD HfO ₂ growth on SiO ₂ ", Atomic Layer Deposition (ALD) 2002, American Vacuum Society Topical Conference, August 19-21, 2002, Hanyang Institute of Technology, Hanyang University, Seoul, Korea		

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10 / 12 / 05

- * A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).
- + An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).